

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application.

1. (original) A method for processing one or more semiconductor wafers, the method comprising the steps of:
providing one or more semiconductor wafers in a processing chamber; and
drying the one or more semiconductor wafers in the processing chamber
wherein during at least a portion of the drying step the one or more semiconductor wafers are in the presence of an antistatic agent.
2. (original) The method of claim 1, wherein the step of drying the one or more semiconductor wafers comprises flowing a drying gas into the processing chamber.
3. (original) The method of claim 2, wherein the drying gas comprises gaseous nitrogen.
4. (original) The method of claim 1, wherein the antistatic agent comprises carbon dioxide.
5. (original) The method of claim 1, wherein the antistatic agent comprises ionized clean dry air.
6. (original) The method of claim 1, wherein the step of drying the one or more semiconductor wafers comprises introducing a drying enhancement substance into the processing chamber.
7. (original) The method of claim 6, wherein the drying enhancement substance comprises isopropyl alcohol.

8. (original) The method of claim 1, further comprising performing at least one additional processing step on the at least one or more semiconductor wafers in the processing chamber.
9. (original) The method of claim 8, wherein the at least one additional processing step comprises a rinsing step that precedes the drying step.
10. (original) The method of claim 9, wherein at least a portion of the rinsing step occurs in the presence of an antistatic agent.
11. (original) The method of claim 10, wherein the antistatic agent comprises a gaseous antistatic agent.
12. (original) The method of claim 10, wherein the antistatic agent comprises solute in a rinsing fluid.
13. (currently amended) The method of ~~claim 10~~claim 11, wherein the gaseous antistatic agent present during at least a portion of the rinsing step comprises carbon dioxide.
14. (currently amended) The method of ~~claim 10~~claim 11, wherein the gaseous antistatic agent present during at least a portion of the rinsing step comprises ionized clean dry air.
15. (cancelled)
16. (cancelled)
17. (cancelled)
18. (cancelled)

19. (cancelled)

20. (cancelled)

21. (cancelled)

22. (cancelled)

23. (cancelled)

24. (cancelled)

25. (original) A method of processing a semiconductor wafer, the method comprising:

- providing a semiconductors wafer in a processing chamber of a spray processor;
- spraying a rinsing fluid onto at least a portion of a surface of the semiconductor wafer in an atmosphere comprising a gaseous antistatic agent; and
- drying at least a portion of the semiconductor wafer in an atmosphere comprising a gaseous antistatic agent.